U.H.F./V.H.F. POWER TRANSISTOR

N-P-N silicon transistor for use in class-B and C operated mobile, industrial and military transmitters with a supply voltage of 13,8 V.

It has a capstan envelope with a moulded cap. All leads are isolated from the stud.

QUICK REFERENCE DATA

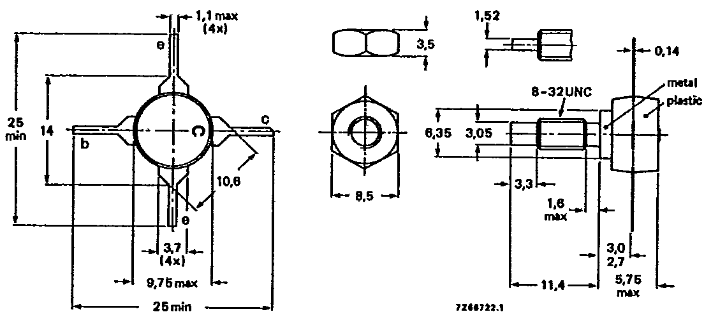
R.F. performance up to T_h = 25 °C in an unneutralized common-emitter class-B circuit

mode of operation	V_{CE} V	f MHz	P_S W	P_L W	I_C A	G_p dB	η %	$\overline{z_i}$ Ω	$\overline{Y_L}$ mS
c.w.	13,8	470	typ. 0,15	1,5	typ. 0,17	typ. 10	typ. 65	–	–
c.w.	13,8	470	typ. 0,35	3,0	typ. 0,28	typ. 9,3	typ. 79	2,9 + j5,1	27 – j21
c.w.	12,5	470	< 0,35	2,5	< 0,31	> 8,5	> 65	–	–
c.w.	12,5	175	typ. 0,03	3,0	typ. 0,29	typ. 20	typ. 84	–	–

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-48/3



Torque on nut: min. 0,75 Nm (7,5 kg cm)
max. 0,85 Nm (8,5 kg cm)

Diameter of clearance hole in heatsink: max. 4,2 mm.
Mounting hole to have no burrs at either end.
De-burring must leave surface flat; do not chamfer or countersink either end of hole.

When locking is required an adhesive is preferred instead of a lock washer.

PRODUCT SAFETY This device incorporates beryllium oxide, the dust of which is toxic. The device is entirely safe provided that the BeO disc is not damaged.

RATINGS Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) peak value	V_{CBOM}	max.	36	V
Collector-emitter voltage (R_{BE} = 0) peak value	V_{CESM}	max.	36	V
Collector-emitter voltage (open base)	V_{CEO}	max.	18	V
Emitter-base voltage (open collector)	V_{EBO}	max.	4	V
Collector current (average)	$I_{C(AV)}$	max.	0.7	A
Collector current (peak value) f > 1 MHz	I_{CM}	max.	2.0	A
Total power dissipation up to T_h = 90 °C f > 10 MHz	P_{tot}	max.	4.5	W
Storage temperature	T_{stg}		−65 to +150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

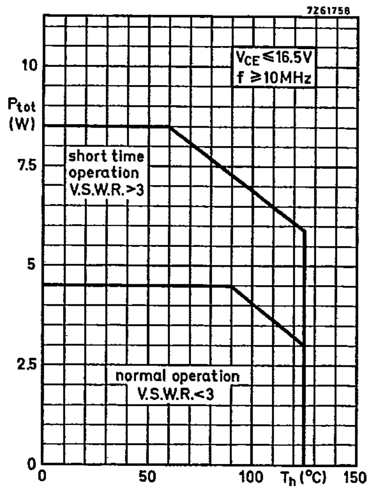
From junction to mounting base	$R_{th\ j-mb}$ =	12	K/W
From mounting base to heatsink	$R_{th\ mb-h}$ =	0.6	K/W

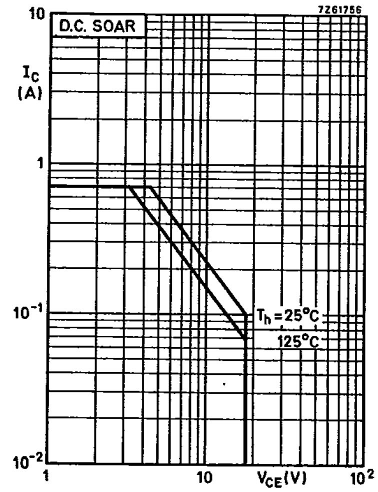
CHARACTERISTICS

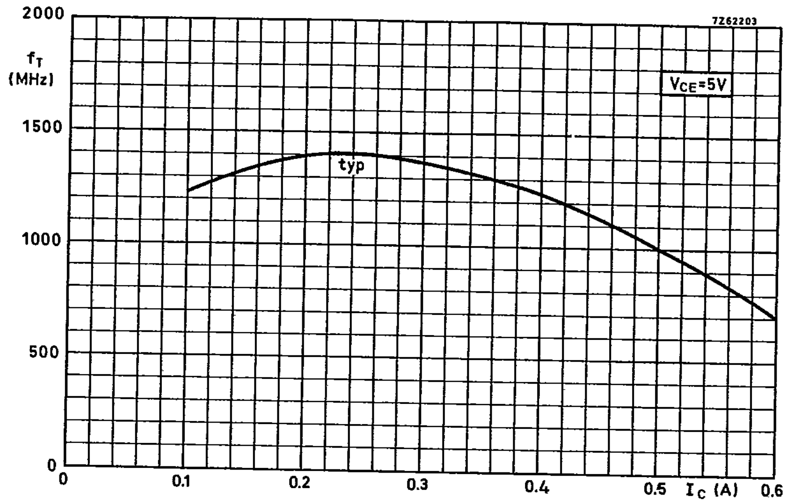
T_j = 25 °C unless otherwise specified

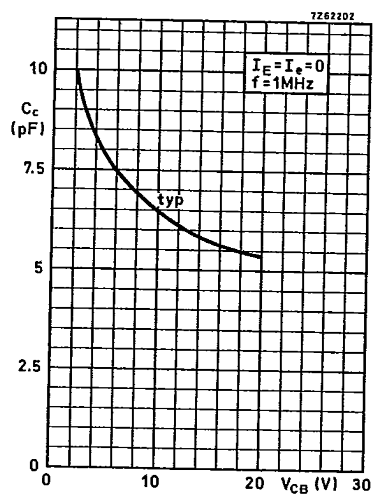
Breakdown voltages

Collector-base voltage open emitter, I_C = 10 mA	$V_{(BR)CBO}$	>	36	V
Collector-emitter voltage V_{BE} = 0; I_C = 10 mA	$V_{(BR)CES}$	>	36	V
Collector-emitter voltage open base, I_C = 25 mA	$V_{(BR)CEO}$	>	18	V
Emitter-base voltage open collector, I_E = 1,0 mA	$V_{(BR)EBO}$	>	4	V
Collector-emitter saturation voltage I_C = 100 mA; I_B = 20 mA	V_{CEsat}	typ.	0,1	V
D.C. current gain I_C = 100 mA; V_{CE} = 5 V	h_{FE}	> typ.	10 40	
Transition frequency I_C = 0,2 A; V_{CE} = 5 V; f = 500 MHz	f_T	typ.	1400	MHz
Collector capacitance at f = 1 MHz I_E = I_e = 0; V_{CB} = 10 V	C_c	typ. <	6,5 9,0	pF pF
Feedback capacitance at f = 1 MHz I_C = 20 mA; V_{CE} = 10 V	C_{re}	typ.	4,8	pF
Collector-stud capacitance	C_{cs}	typ.	2	pF


7Z61758
V_{CE}≤16.5V
f ≥10MHz
P_{tot}
(W)
10
7.5
5
2.5
0
short time
operation
V.S.W.R.>3
normal operation
V.S.W.R.<3
0
50
100
T_h (°C)
150


7Z61756
D.C. SOAR
I_C
(A)
10
1
10^{-1}
10^{-2}
T_h = 25°C
125°C
1
10
V_{CE}(V)
10^2


7Z62203
f_T (MHz)
2000
1500
1000
500
0
V_{CE}=5V
typ
0
0.1
0.2
0.3
0.4
0.5
I_C (A)
0.6


7Z62202
C_c (pF)
10
7.5
5
2.5
0
I_E=I_e=0
f=1MHz
typ
0
10
20
V_{CB} (V)
30

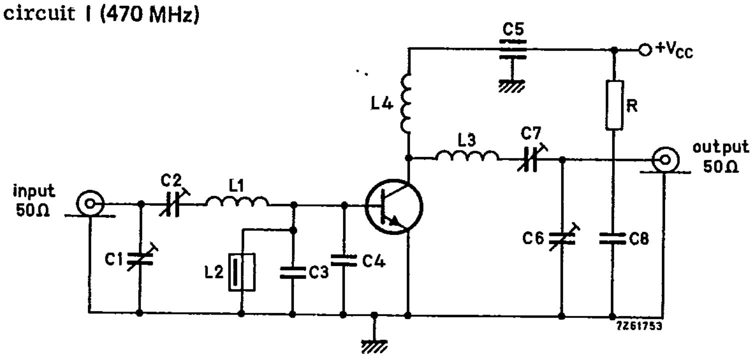
APPLICATION INFORMATION T_j = 25 °C unless otherwise specified

R.F. performance in c.w. operation (unneutralized common-emitter class B circuit)

T_h up to 25 °C

f (MHz)	V_{CC} (V)	P_S (W)	P_L (W)	I_C (A)	G_p (dB)	η (%)	$\bar{z}_i$ (Ω)	$\bar{Y}_L$ (mS)
470	13.8	typ. 0.15	1.5	typ. 0.17	typ. 10	typ. 65	-	-
470	13.8	typ. 0.35	3.0	typ. 0.28	typ. 9.3	typ. 79	2.9 + j5.1	27 − j21
470	12.5	< 0.35	2.5	< 0.31	> 8.5	> 65	-	-
175	12.5	typ. 0.03	3.0	typ. 0.29	typ. 20	typ. 84	-	-

Test circuit I (470 MHz)



C1 = C2 = C6 = C7 = 1.8 to 18 pF film dielectric trimmer
C3 = C4 = 18 pF disc ceramic capacitor
C5 = 4 nF feed-through capacitor
C8 = 0.1 μF polyester capacitor

L1 = 1 turn Cu wire (1.2 mm); int. diam. 6 mm; max. lead length 1 mm
L2 = 1 μH choke
L3 = 30 mm straight Cu wire (2 mm); height above print 2 mm
L4 = 2 turns closely wound Cu wire (0.5 mm); int. diam. 3 mm; max. lead length 8 mm

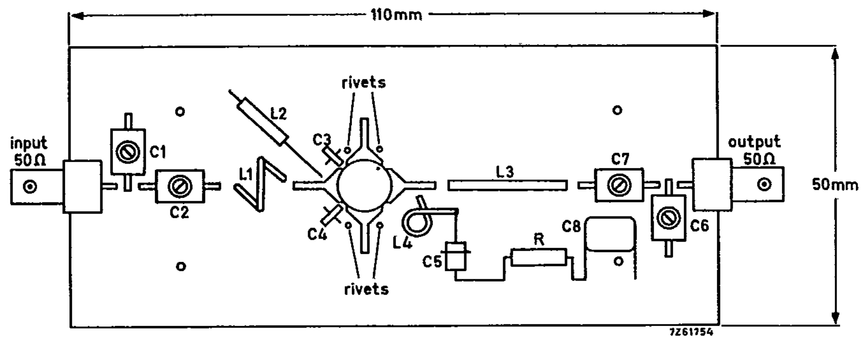
R = 10 Ω carbon

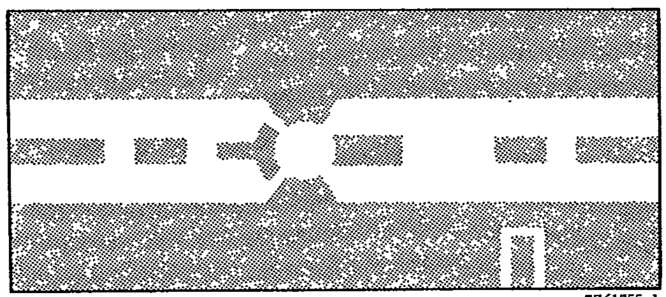
At P_L = 2.5 W and V_{CC} = 12.5 V, the output power at heatsink temperatures between 25 °C and 90 °C relative to that at 25 °C is diminished by typ. 5 mW/K

The transistor is designed to withstand full load mismatch in the test circuit under the following conditions: V_{CC} = 16.5 V; f = 470 MHz; T_h = 70 °C;
V.S.W.R. = 50 : 1 through all phases; $P_S = P_{Snom}$ + 20 %
where $P_{Snom} = P_S$ for 2.5 W transistor output into 50 Ω load and V_{CC} = 13.8 V

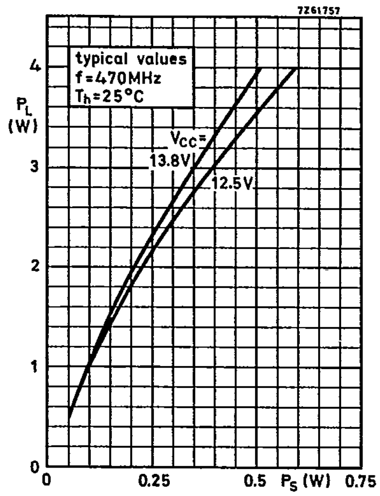
APPLICATION INFORMATION (continued)

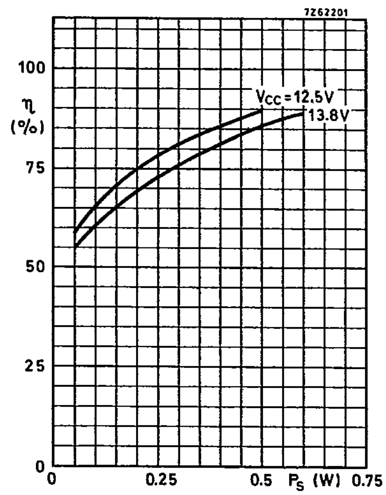
Component lay-out and printed circuit board for 470 MHz test circuit.

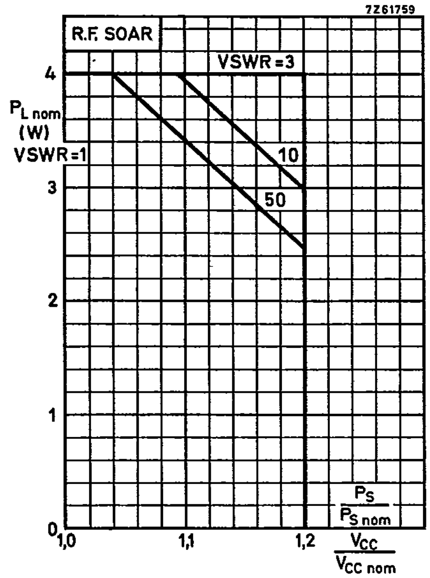




Shaded area copper
Back area completely copper clad.
Material of printed circuit board: 1,5 mm epoxy fibre glass.


7Z61757
typical values
f=470MHz
T_h=25°C
P_L
(W)
V_{CC}=
13.8V
12.5V
0
1
2
3
4
0
0.25
0.5
P_S (W)
0.75


7Z62201
100
η
(%)
75
50
25
0
V_{CC}=12.5V
13.8V
0
0.25
0.5
P_S (W)
0.75



Conditions for R.F. SOAR

f = 470 MHz

T_h = 70 °C

V_{CCnom} = 13,8 V

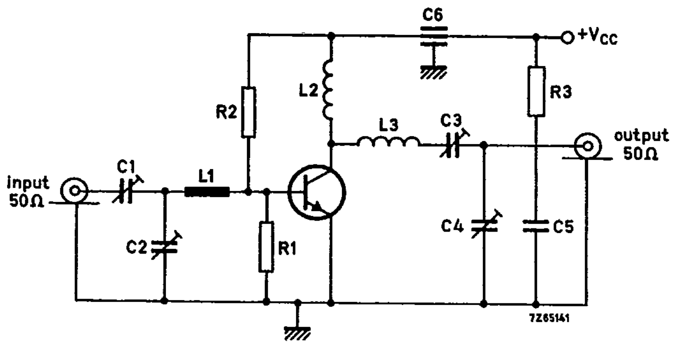
$P_{Snom} = P_S$ at $V_{CC} = V_{CCnom}$ and VSWR = 1

$R_{th\,mb\text{-}h}$ = 0,6 K/W

The transistor was developed for use with unstabilized supply voltage V_{CC}.
The above graph is based on its measured performance in test circuit I.
Supply voltage was varied from V_{CCnom} to 1,2 V_{CCnom}, and VSWR from 1 to 50.
It shows the max. permissible output power under nominal conditions in order not to exceed the max. permissible power dissipation under conditions of supply over-voltage ($V_{CC} > V_{CCnom}$) and load mismatch (VSWR > 1).
It is assumed that the drive power increases linearly with the supply voltage; i.e. $P_S/P_{Snom} = V_{CC}/V_{CCnom}$.

APPLICATION INFORMATION (continued)

Test circuit II (175 MHz)



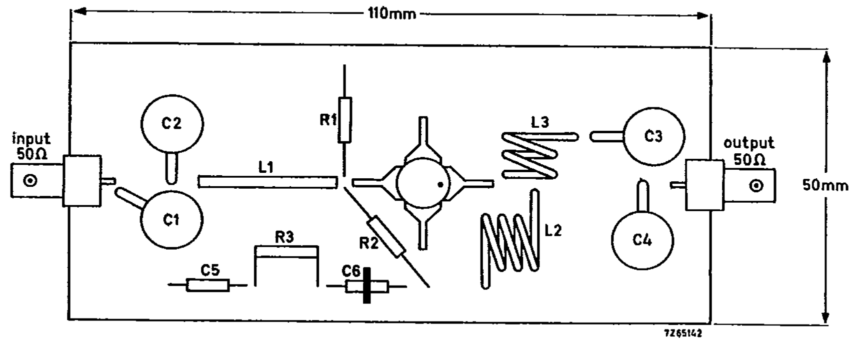
C1 = C3 = C4 = 30 pF concentric air trimmer
C2 = 60 pF concentric air trimmer
C5 = 0.25 μF ceramic capacitor
C6 = 4 nF polyester capacitor

L1 = 25 mm straight Cu wire (1.2 mm); height above print max. 3 mm
L2 = 3 turns closely wound Cu wire (1.2 mm); int. diam. 10 mm; lead length 5 mm
L3 = 2 turns closely wound Cu wire (1.7 mm); int. diam. 12 mm; lead length 5 mm

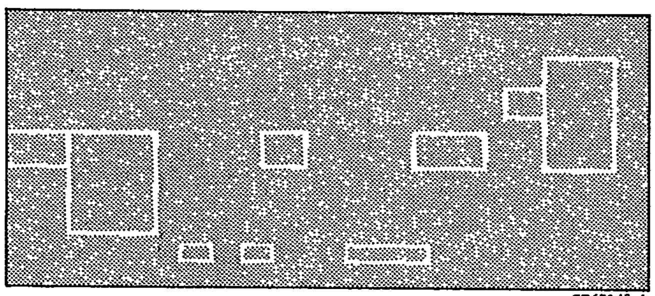
R1 = 50 Ω carbon
R2 = 1.2 kΩ carbon
R3 = 5 Ω carbon

APPLICATION INFORMATION (continued)

Component lay-out and printed circuit board for 175MHz test circuit.



Shaded area copper
Back area not metalized
Material of pcb : 1.5 mm epoxy fibre glass



7Z65143.1

OPERATING NOTE Below 200 MHz a base-emitter resistor of 10 Ω is recommended to avoid oscillation. This resistor must be effective for both d.c. and r.f.